

ON Semiconductor

Is Now

onsemi™

To learn more about onsemi™, please visit our website at
www.onsemi.com

onsemi and **onsemi** and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi** product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner. Other names and brands may be claimed as the property of others.

Thermal Sensing Methods used in ON Semiconductor Devices



ON Semiconductor®

<http://onsemi.com>

APPLICATION NOTE

Introduction

This application note will describe the standard methods used by ON Semiconductor devices for temperature measurement. It will also discuss the various sources of error that arise and the techniques used to minimize them.

Transistor Basics

For a given collector current, I_c , the basic equation that relates the temperature of a transistor to the base-emitter voltage V_{be} is:

$$T := \frac{q \cdot V_{be}}{K \cdot \ln\left(\frac{I_c}{I_s}\right)} \quad (\text{eq. 1})$$

where:

- T is the absolute temperature in degrees Kelvin
- K is Boltzmann's constant ($1.38 \times 10^{-23} \text{ JK}^{-1}$)
- q is the charge on the electron (1.6×10^{-19} coulombs)
- I_c is the collector current
- I_s is the reverse saturation current

Theoretically this equation can be used to determine the transistor temperature by setting I_c and measuring the base-emitter voltage. In practice this leads to large errors due to the dependence of the equation on I_s , which can vary widely between transistors. In order to cancel out the dependency on I_s and get a more accurate temperature measurement, a different technique is required.

2-Current Sensing Method

The method used to eliminate dependence on I_s is to switch 2 currents through the transistor and measure V_{be} for each one. The difference in V_{be} measurements can then be used to determine the transistor temperature.

Re-arranging Equation 1 to get V_{be} gives:

$$V_{be} := \frac{K \cdot T}{q} \cdot \ln\left(\frac{I_c}{I_s}\right) \quad (\text{eq. 2})$$

The difference in V_{be} for 2 currents, where I_{c1} is the high level current and I_{c2} is the low level current, is:

$$V_{be1} - V_{be2} := \frac{K \cdot T}{q} \cdot \left(\ln\left(\frac{I_{c1}}{I_s}\right) - \ln\left(\frac{I_{c2}}{I_s}\right) \right) \quad (\text{eq. 3})$$

which gives:

$$V_{be1} - V_{be2} := \frac{K \cdot T}{q} \cdot \ln\left(\frac{I_{c1}}{I_{c2}}\right) \quad (\text{eq. 4})$$

Setting I_{c1} as a fixed multiple, N, of I_{c2} gives:

$$\Delta V_{be} := \frac{K \cdot T}{q} \cdot \ln(N) \quad (\text{eq. 5})$$

This is the equation used internally in 2-current ON Semiconductor devices to calculate temperature based on the difference in V_{be} measurements. The typical value used for N is 17. The internal circuitry used in 2-current devices is shown in Figure 1.

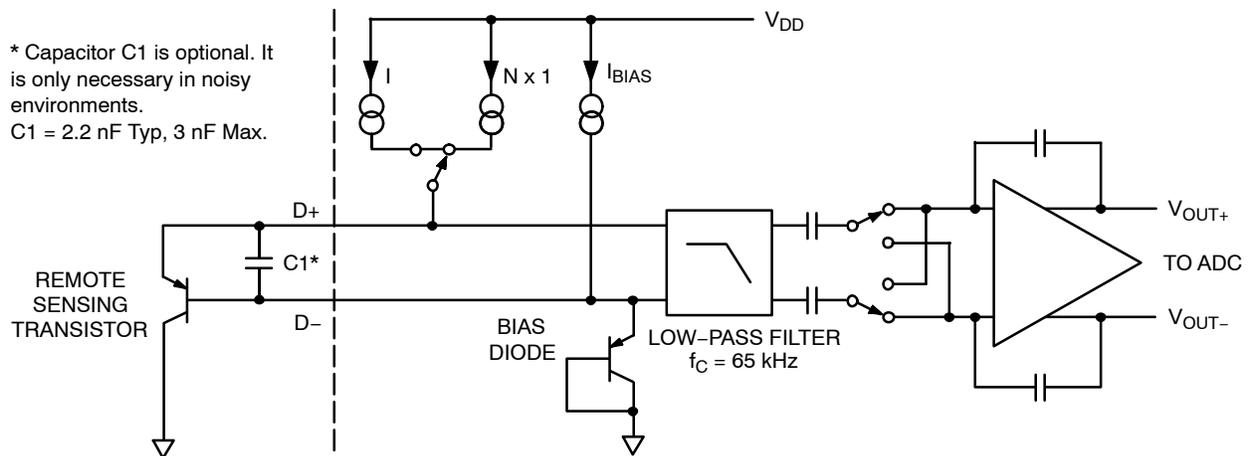


Figure 1. Internal Circuit for 2-current Device

AND8494/D

As can be seen in Figure 1, there is an internal low pass filter to help with noise immunity. Typically the D- pin is biased above ground, which also helps to protect against noise interference. Figure 1 shows a diode connected transistor as the biasing element. Some devices use a resistor as the biasing element to reduce the biasing voltage. The

connection of the remote sensor as shown in Figure 1 is for an internal sensor on a processor. If using a discrete transistor it must be connected as a diode-connected transistor. Connections for NPN or PNP transistors are shown in Figure 2.

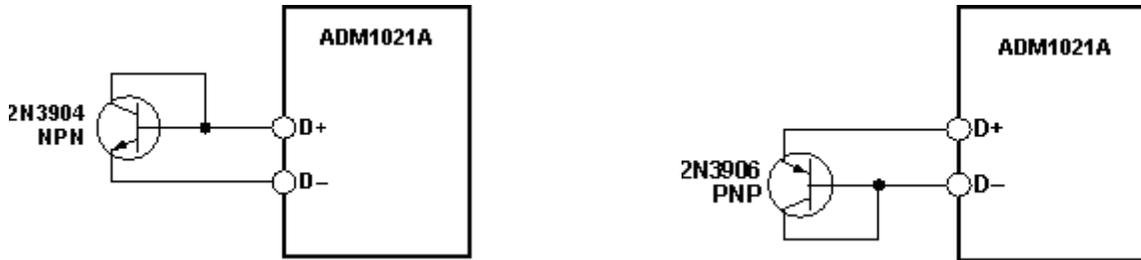


Figure 2. Connections for Discrete NPN and PNP Transistors

The typical D+ and D- waveforms for a 2-current device are shown in Figure 3.

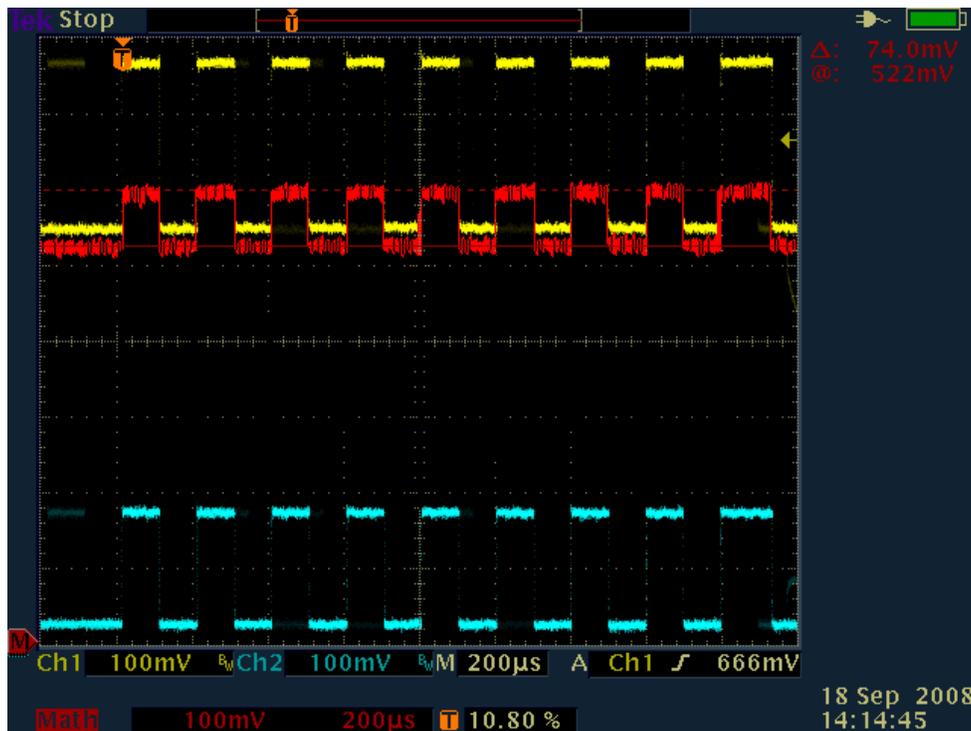


Figure 3. D+/D- Waveforms for a 2-current Device

In Figure 3 the yellow trace is D+, the blue trace is D- and the red trace is the differential voltage. The differential voltage here is ~74 mV which is typical for room temperature.

Sources of Error in Temperature Measurement

In order for a stable reading to be made it is usual for the device to take multiple measurements and average the results. This digital filtering reduces variations from reading to reading, but there are other factors that can introduce errors that must be taken into account. These are:

- nf, the transistor non-ideality factor

- High frequency noise
- Capacitance across D+/D-
- Series Resistance

Errors due to non-ideality factor nf:

Equation 5 assumes an ideal transistor. Most transistors deviate from the ideal model, and this deviation is taken into account by adding a correction factor, nf, to the equation.

$$\Delta V_{be} := \frac{nf \cdot K \cdot T}{q} \cdot \ln(N) \quad (\text{eq. 6})$$

On Semiconductor devices use a value of 1.008 as the nf value when calculating temperature. The difference between a transistors actual nf value and the assumed 1.008 nf value will give rise to a temperature error. This error can be seen in Figure 4.

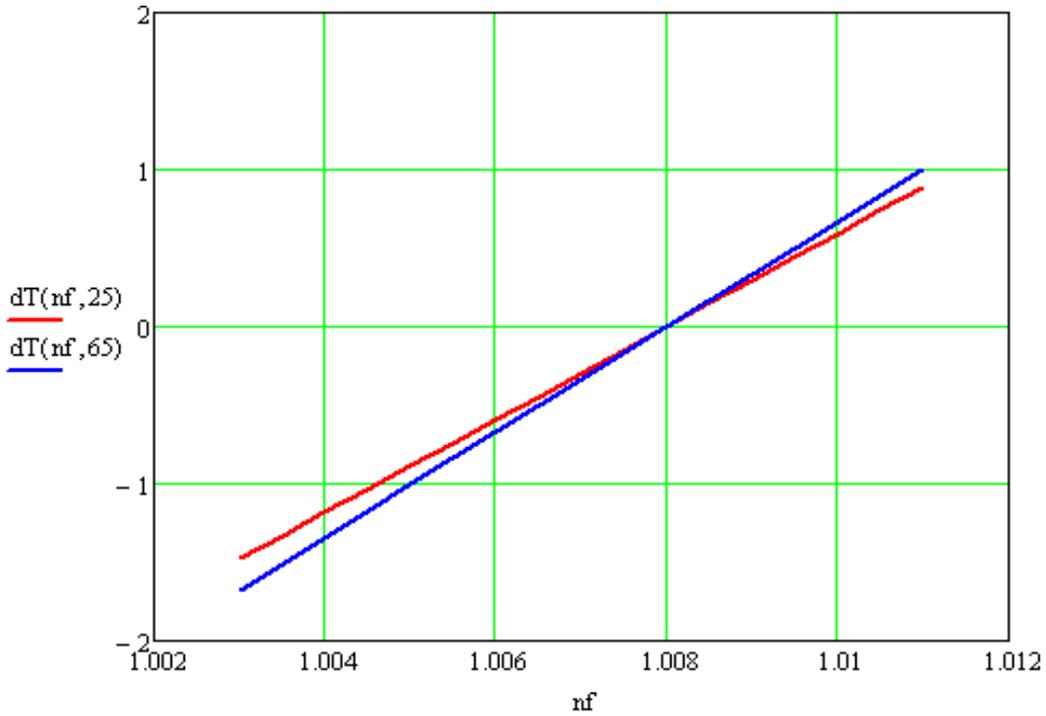


Figure 4. Temperature Error due to nf Variations at 25°C and 65°C

In Figure 4 the red plot is the error over a range of nf values at 25°C and the blue plot is the error for a range of nf values at 65°C.

Errors due to high frequency noise:

In a noisy environment like a motherboard the D+/D- lines can pick up interference which can introduce errors into the temperature measurement. This interference can be

reduced by taking care with the layout of the D+/D- lines. The lines should be routed together to reduce differential noise and especially noisy sections of the motherboard should be avoided if possible. Ground plane shielding should also be used to reduce interference. Typical error curves for common mode and differential mode noise are shown in Figure 5.

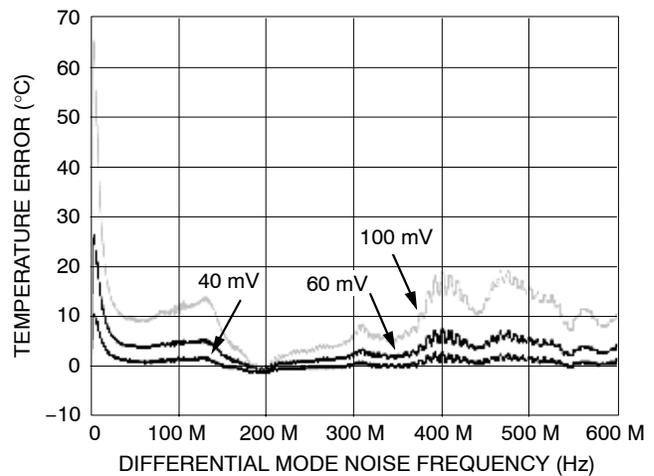
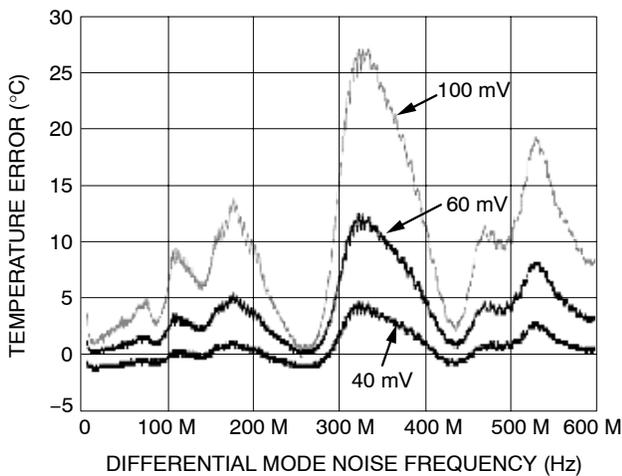


Figure 5. Temperature Error due to Common Mode and Differential Mode Noise

Errors due to capacitance across D+/D-:

In order to help reduce noise interference it is common to put a capacitor across the D+ and D- lines close to the device. Care must be taken with the chosen capacitor value as the devices are sensitive to this capacitance, and large errors can be introduced if an inappropriate value is used. A typical plot of temperature error due to D+/D- capacitance is shown in Figure 6.

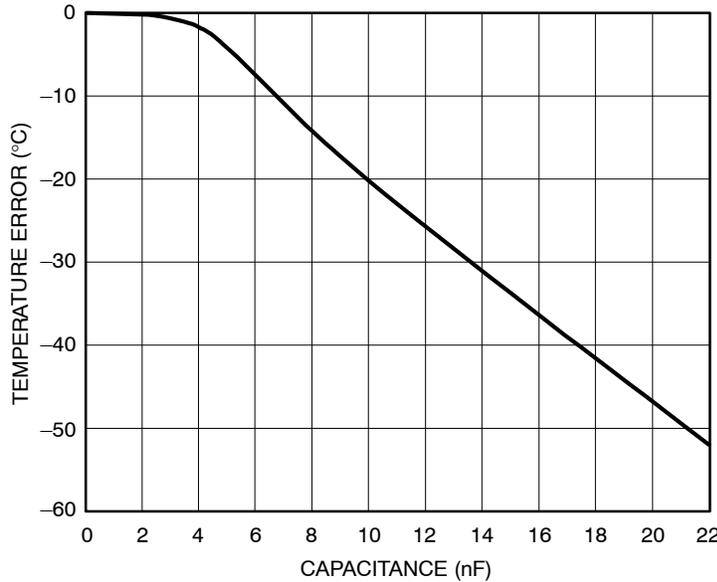


Figure 6. Temperature Error due to D+/D- Capacitance

Errors due to series resistance:

Any resistance that is in series with the sensing diode will introduce an error in the temperature measurement with a 2-current device. The switched current sources will cause a voltage drop across the series resistance which will be seen as an offset. Because of this the magnitude of the temperature error will depend on both the series resistance and the values of the high and low currents being switched through the transistor. The temperature error can be calculated using:

$$\text{Temperature Error} := \frac{(I1 - I2) \cdot R \cdot q}{k \cdot nf \cdot \ln(N)} \quad (\text{eq. 7})$$

where:

- I1 is the high level current
- I2 is the low level current
- R is the series resistance
- q, K, nf and N are as previously defined

Example: The ADT7481 is a 2-current device with a high level current of 233 μA and a low level current of 13 μA. For a series resistance of 4 Ω the expected voltage error will be (233 μA - 13 μA)*4 = 0.88 mV which will translate into a temperature error of 3.5°C.

The effect of series resistance on 2-current devices prevents the use of a low pass filter on D+/D- to help with noise issues. Although internal offset registers can be used to correct small offset errors, for useful filters the resistor must be as large as possible due to the limitation on the allowable capacitor values across D+/D-, so the error due to the resistance will be large. To address this, another method of temperature sensing must be used

3-Current Sensing Method

The method used to eliminate the offset due to series resistance is to add a 3rd current source to the switching cycle. Figure 7 shows the internal structure of a 3-current device. By adding a 3rd current to the sequence it can be shown that, with a carefully chosen measurement sequence, the measurement is independent of resistance in the sensor path, typically up to 3 kΩ. As well as removing errors due to parasitic resistance it also allows relatively large value resistors to be added to D+ and D- to form a low pass filter to reduce the effects of noise.

Definitions:

- K = Boltzmann's Constant
- q = electron charge
- n = non-ideality factor
- I1 = Low level current
- I2 = Mid level current
- I3 = High Level Current
- N21 = Ratio of I2 to I1
- N31 = Ratio of I3 to I1
- Vbe1 = Vbe with Ie = I1
- Vbe2 = Vbe with Ie = I2
- Vbe3 = Vbe with Ie = I3
- ΔVbe21 = Vbe2 - Vbe1
- ΔVbe32 = Vbe3 - Vbe2
- Re = Resistance in emitter path
- Rb = Resistance in base path

AND8494/D

The differential base emitter voltage for low and mid currents is given by:

$$\Delta V_{be21}(T) := \frac{n \cdot K \cdot T}{q} \cdot \ln(N21) + I1 \cdot (N21 - 1) \cdot \left(R_e + \frac{R_b}{\beta + 1} \right)$$

The differential base emitter voltage for mid and high currents is given by:

$$\Delta V_{be32}(T) := \frac{n \cdot K \cdot T}{q} \cdot \ln\left(\frac{N31}{N21}\right) + I1 \cdot (N31 - N21) \cdot \left(R_e + \frac{R_b}{\beta + 1} \right)$$

Apply a gain of A to ΔV_{be21} and B to ΔV_{be32} then calculate the difference:

$$A \cdot \Delta V_{be21}(T) - B \cdot \Delta V_{be32}(T) := \frac{n \cdot K \cdot T}{q} \cdot \ln\left(\frac{N21^{A+B}}{N31^B}\right) + I1 \cdot \left(R_e + \frac{R_b}{\beta + 1} \right) \cdot [A \cdot (N21 - 1) - B(N31 - N21)]$$

Therefore, if the following condition is met, the above expression is independent of path resistance:

$$A \cdot (N21 - 1) := B \cdot (N31 - N21)$$

Selecting B to be 1, A is given by:

$$A := \frac{N31 - N21}{N21 - 1}$$

Using this value for A, the temperature (in Celsius) of the transistor can be calculated from:

$$T := \frac{(A \cdot \Delta V_{be21} - \Delta V_{be32}) \cdot q}{n \cdot K \cdot \ln\left(\frac{N21^{A+1}}{N31}\right)} - 273$$

Figure 8 shows the typical D+ and D- waveforms for a 3-current device.

Figure 9 shows the connection for a low pass filter on D+ and D-.

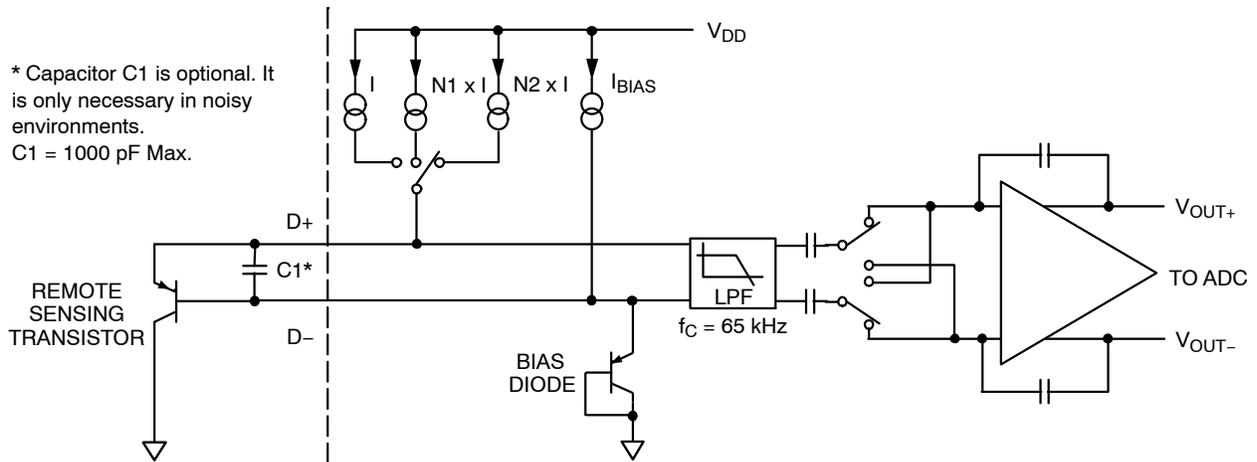


Figure 7. Internal Circuit for 3-current Device

Table 1. 2-CURRENT AND 3-CURRENT TEMPERATURE SENSING DEVICES

Device	# Remote Channels	# Currents	Accuracy	Supply Voltage
ADM1032	1	2	±1°C	3 – 5.5 V
ADT7461	1	3	±1°C	3 – 5.5 V
ADT7461A	1	3	±1°C	3 – 3.6 V
ADT7481	2	2	±1°C	3 – 3.6 V
ADT7482	2	3	±1°C	3 – 3.6 V
ADT7483A	2	2	±1°C	3 – 3.6 V
ADT7484A	1	3	±1°C	3 – 3.6 V
ADT7485A	1	3	±1°C	3 – 3.6 V
ADT7486A	2	3	±1°C	3 – 3.6 V
ADT7488A	2	3	±1°C	3 – 3.6 V
NCT1008	1	3	±1°C	2.8 – 3.6 V



Figure 8. Typical D+/D- Waveforms for 3-current Device

In Figure 8 the yellow trace is D+, the blue trace is D- and the red trace is the differential voltage.

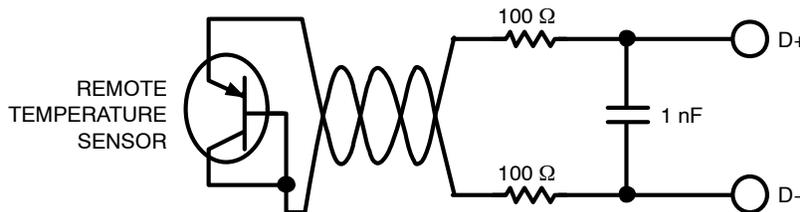


Figure 9. Low Pass Filter Added for Noise Immunity

ON Semiconductor and are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
 Literature Distribution Center for ON Semiconductor
 P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
 Phone: 421 33 790 2910
Japan Customer Focus Center
 Phone: 81-3-5773-3850

ON Semiconductor Website: www.onsemi.com
Order Literature: <http://www.onsemi.com/orderlit>
 For additional information, please contact your local Sales Representative